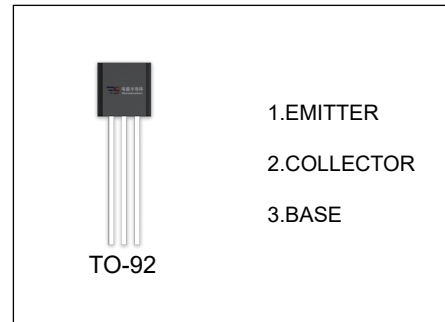


## 2SD2152 TRANSISTOR (NPN)

### FEATURES

- High DC Current Gain
- Low Saturation Medium Current Application



### ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SD2152	TO-92	Bulk	1000pcs/Bag
2SD2152-TA	TO-92	Tape	2000pcs/Box

### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	22	V
$V_{CEO}$	Collector-Emitter Voltage	22	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	3	A
$P_C$	Collector Power Dissipation	700	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	178	$^{\circ}\text{C}/\text{W}$
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

$T_a=25\text{ }^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.05\text{mA}, I_E=0$	22			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	22			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01\text{mA}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=20\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=0.15\text{mA}$	130			
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=100\text{mA}$	180		950	
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=500\text{mA}$	180			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2000\text{mA}, I_B=100\text{mA}$			0.4	V
Transition frequency	$f_T$	$V_{CE}=6\text{V}, I_C=50\text{mA}, f=30\text{MHz}$	150			MHz

#### CLASSIFICATION OF $h_{FE}$

RANK	Q	R	S	T
RANGE	180-290	270-380	340-560	560-950